

FEATURES

- 1.2 mm square active area
- Low dark current
- Long term stability
- High shunt resistance

DESCRIPTION

1.44 mm² active area High Shunt Resistance Photodiode with P on N construction. Low cost solution packaged in a ceramic header with a clear epoxy dome lens.

APPLICATIONS

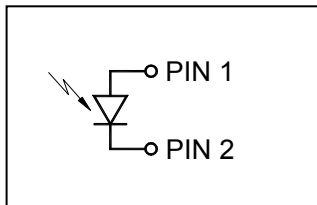
- Bar code readers
- Optical switches
- Optical remote control
- Pulsed light sensor



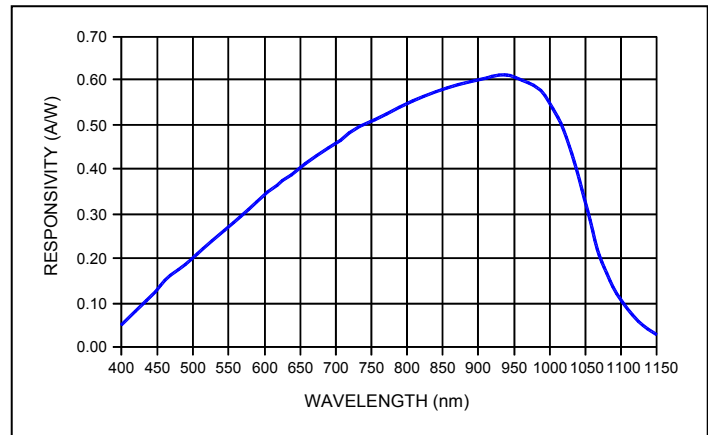
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-15	+100	°C
T _{OP}	Operating Temp	0	+70	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _{SH}	Shunt Resistance	V _R = ±10 mV	2	20	---	GΩ
I _D	Dark Current	V _R = 10 V	---	10	100	pA
C	Capacitance	V _R = 10 V	---	20	---	pF
	Responsivity	V _R = 0 V; λ = 450 nm	---	0.14	---	A/W
		V _R = 0 V; λ = 850 nm	---	0.58	---	
NEP	Noise Equivalent Power	V _R = 0 V; λ = 850 nm; R _L = 50 Ω	---	1.8 X 10 ⁻¹⁵	---	W/Hz ^{1/2}
V _{BR}	Breakdown Voltage	I _R = 10 μA	50	---	---	V
t _r	Rise Time	V _R = 0 V; λ = 850 nm; R _L = 50 Ω	---	2	---	μs

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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